

Electronic Supplementary Information

Active and Dynamic Infrared Switching of VO₂ (M) Nanoparticles Film on ITO Glass

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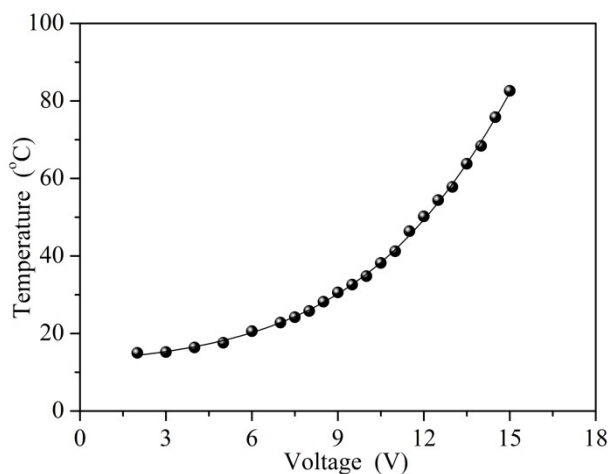


Fig. S1 Temperature profile of ITO glass substrate upon applied voltage. One can see the temperature increases with increasing applied voltage and is over 80 °C at 15 V, which is higher than the phase transition temperature of VO₂ (M).

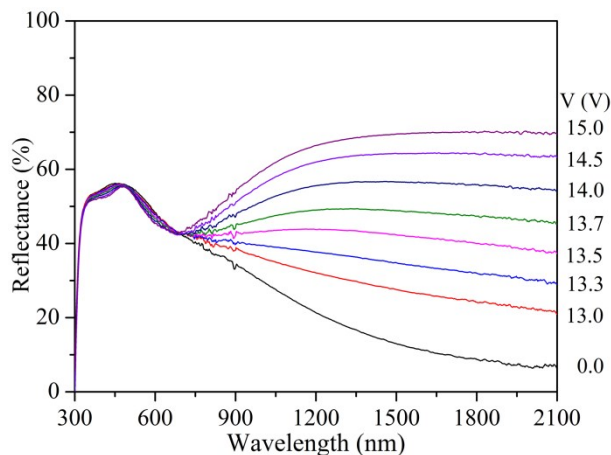


Fig. S2 Dependence of reflectance of V3 device on the applied voltage. The reflectance was calculated from transmittance (R) and absorption (A) in Fig. 3 by the formula $R+T+A=1$. One can see the reflectance increases with increasing input voltage, which is different from our previous work (reference 26), in which the reflectance was directly measured by UV-3600 spectrophotometer with diffuse reflection mode and decreases with increasing input voltage.